

## High Voltage Half Bridge Gate Drive IC

### General description

The ID7U603 is a high voltage, high speed power MOSFET and IGBT driver based on P<sub>sub</sub>P<sub>epi</sub> process. The floating channel driver can be used to drive two N-channel power MOSFETs or IGBTs in a half-bridge configuration which operates up to 600V. Logic inputs are compatible with standard CMOS or LSTTL output, down to 3.3V logic. The output drivers feature a high pulse current buffer stage designed for minimum driver cross-conduction. Propagation delays are matched to simplify use in high frequency applications.

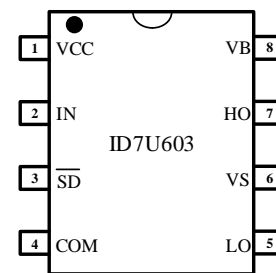
### Application

- Small and medium-power motor driver
- Power MOSFET or IGBT driver
- Lighting ballast
- Half-Bridge Power Converters
- Full-Bridge Power Converters

### Features

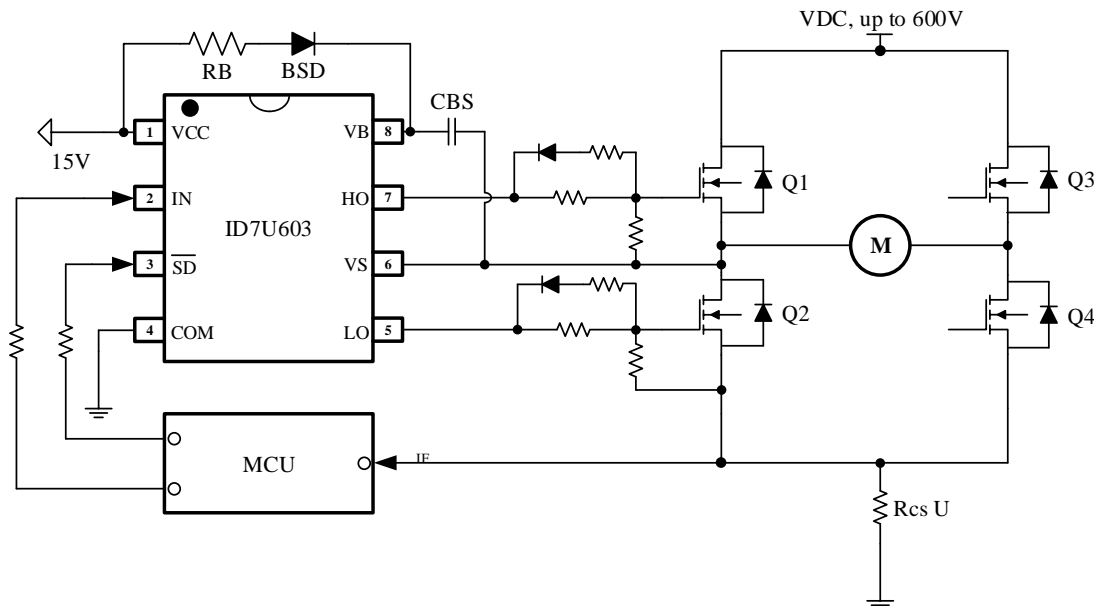
- Operation to +600 V
- Typically 210 mA/360 mA Source/Sink current
- 5 V and 3.3 V input logic compatible
- dV/dt Immunity ±50 V/nsec
- Gate drive supply range from 10 V to 20 V
- UVLO for VCC and VBS
- Cross-conduction prevention logic with 520ns internal fixed Dead time
- Matched propagation delay for all channels

### Package/Order Information



Order code	Package
ID7U603SEC-R1	SOP8

### Typical Application Circuit



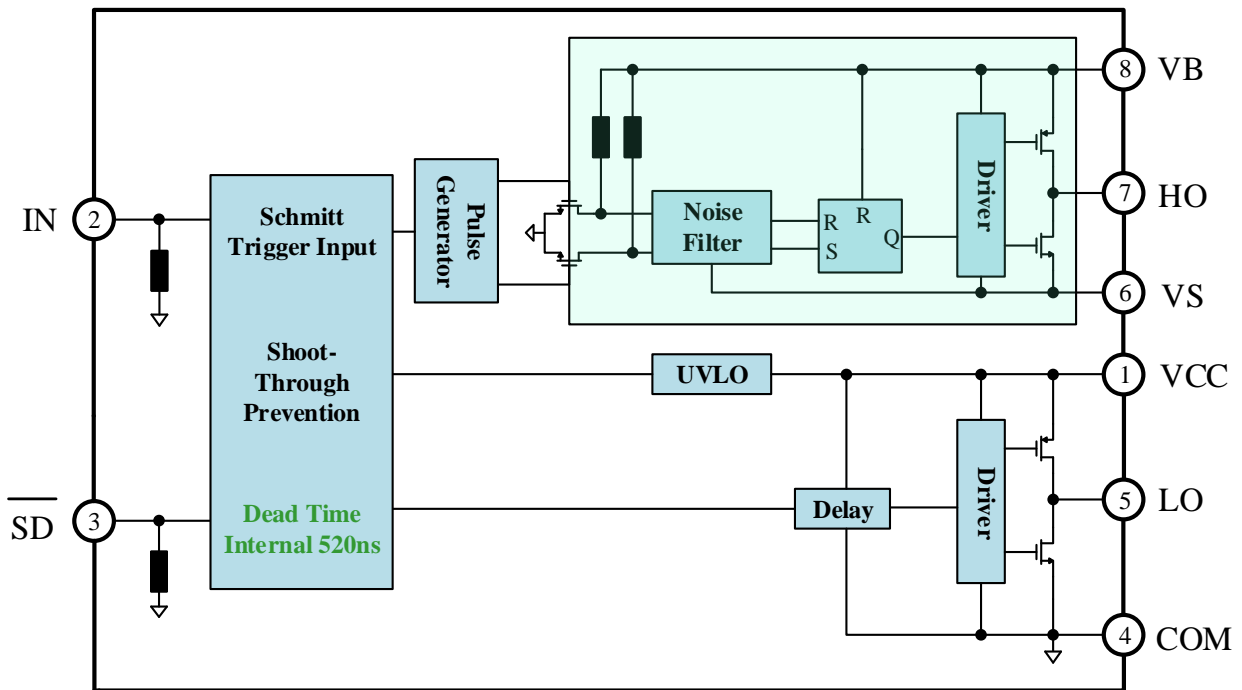
Note 1:

Add RB between VCC and Bootstrap Diode, to avoid VB-VS over-shoot when CBS is charged first time. The recommended value for RB is 10 ohm.

## Pin Definitions

Pin Name	Pin Number	Pin Function Description
VCC	1	Low side and main power supply
IN	2	Logic input for high and low side gate driver outputs (HO and LO)
$\overline{SD}$	3	Logic input for shutdown
COM	4	Low side return
LO	5	Low side gate drive output, Out phase with LIN
VS	6	High side floating supply return or bootstrap return
HO	7	High side gate drive output, in phase with HIN
VB	8	High side floating supply

## Functional Block Diagram



## Absolute Maximum Ratings

Exceeding these ratings may damage the device.

The absolute maximum ratings are stress ratings only at  $T_A=25\text{ }^\circ\text{C}$ , unless otherwise specified.

Symbol	Definition	MIN.	MAX.	Units
$V_B$	High side floating supply	-0.3	620	V
$V_S$	High side floating supply return	$V_B - 20$	$V_B + 0.3$	
$V_{HO}$	High side gate drive output	$V_S - 0.3$	$V_B + 0.3$	
$V_{CC}$	Low side and main power supply	-0.3	20	
$V_{LO}$	Low side gate drive output	-0.3	$V_{CC} + 0.3$	
$V_{IN}$	Logic input of IN and $\overline{SD}$	-0.3	$V_{CC} + 0.3$	
dVs/dt	Allowable Offset Supply Voltage Transient	—	50	V/ns
ESD	HBM Model	2	—	kV
	Machine Model	200	—	V
$P_D$	Package Power Dissipation @ $T_A \leq 25^\circ\text{C}$ (8 Lead SOP)	—	0.625	W
$R_{thJA}$	Thermal Resistance Junction to Ambient (8 Lead SOP)	—	200	$^\circ\text{C}/\text{W}$
$T_J$	Junction Temperature	—	150	$^\circ\text{C}$
$T_S$	Storage Temperature	-55	150	
$T_L$	Lead Temperature (Soldering, 10 seconds)	—	300	

## Recommended Operating Conditions

Symbol	Definition	Min.	Max.	Units
$V_B$	High side floating supply	$V_S + 10$	$V_S + 20$	V
$V_S$	High side floating supply return	-	600	
$V_{HO}$	High side gate drive output voltage	$V_S$	$V_B$	
$V_{CC}$	Low side supply	10	20	
$V_{LO}$	Low side gate drive output voltage	0	$V_{CC}$	
$V_{IN}$	Logic input voltage(IN & $\overline{SD}$ )	0	$V_{CC}$	
$T_A$	Ambient temperature	-40	125	$^\circ\text{C}$

## Dynamic Electrical Characteristics

( $V_{BIAS}$  ( $V_{CC}$ ,  $V_{BS}$ ) = 15V,  $C_L$  = 1000 pF and  $T_A$  = 25 °C unless otherwise specified.)

Symbol	Definition	MIN.	TYP.	MAX.	Units
$t_{on}$	High side turn-on propagation delay	-	680	820	ns
$t_{off}$	High side turn-off propagation delay	-	150	220	
$t_{SD}$	Low side turn-on propagation delay	-	160	220	
MT	Delay matching	-	-	60	
DT	Dead time	400	520	650	
$t_r$	Turn-on rise time	-	100	170	
$t_f$	Turn-off fall time	-	50	90	

## Static Electrical Characteristics

( $V_{BIAS}$  ( $V_{CC}$ ,  $V_{BS}$ ) = 15V,  $C_L$  = 1000 pF and  $T_A$  = 25 °C unless otherwise specified.)

Symbol	Definition	MIN.	TYP.	MAX.	Units
$V_{IH}$	Logic "1" ( $IN$ & $\overline{SD}$ ) input voltage	2.5	-	-	V
$V_{IL}$	Logic "0" ( $IN$ & $\overline{SD}$ ) input voltage	-	-	0.8	
$V_{OH}$	High level output voltage, $V_{BIAS} - V_O$	-	-	0.3	
$V_{OL}$	Low level output voltage, $V_O$	-	-	0.3	
$I_{QCC}$	Quiescent $V_{CC}$ supply current	-	150	270	uA
$I_{QBS}$	Quiescent $V_B$ supply current	-	30	55	
$I_{LK}$	Leakage current from $V_S(600V)$ to GND	-	-	10	
$I_{IN+}$	Logic "1" input bias current	-	6	10	
$I_{IN-}$	Logic "0" input bias current	-	-	1	
$V_{CCU+}$	$V_{CC}$ supply UVLO threshold	-	8.9	-	V
$V_{CCU-}$		-	8.2	-	
$I_{O+}$	Output high short circuit pulsed current	130	210	-	mA
$I_{O-}$	Output low short circuit pulsed current	270	360	-	

## Function Timing Diagram

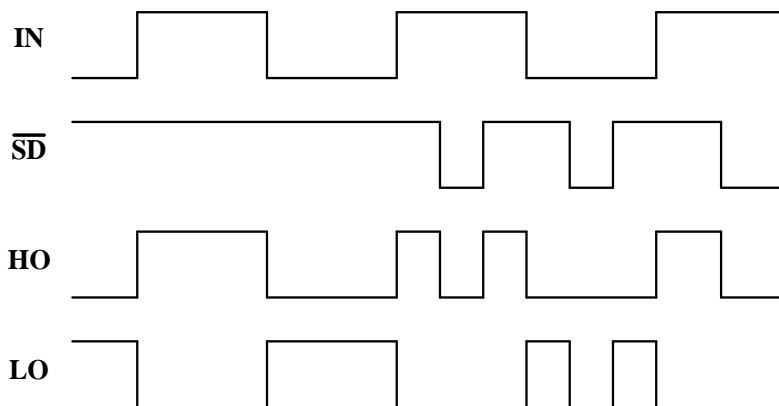


Fig.1 Input/output timing waveform

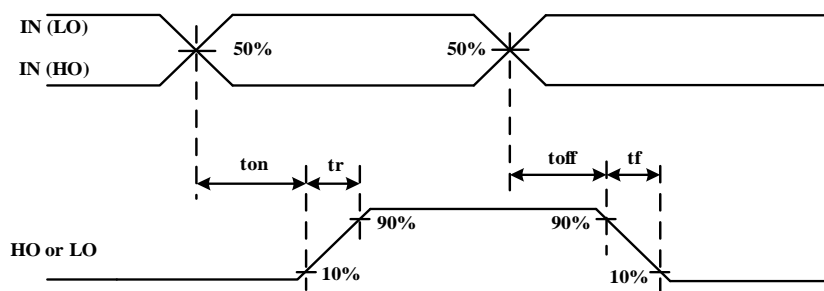


Fig.2 Switching time waveform definitions

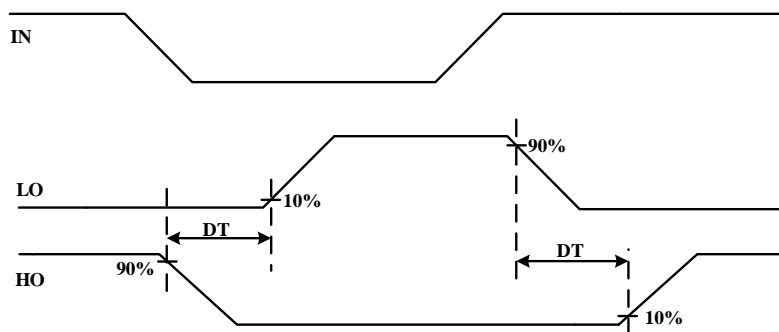
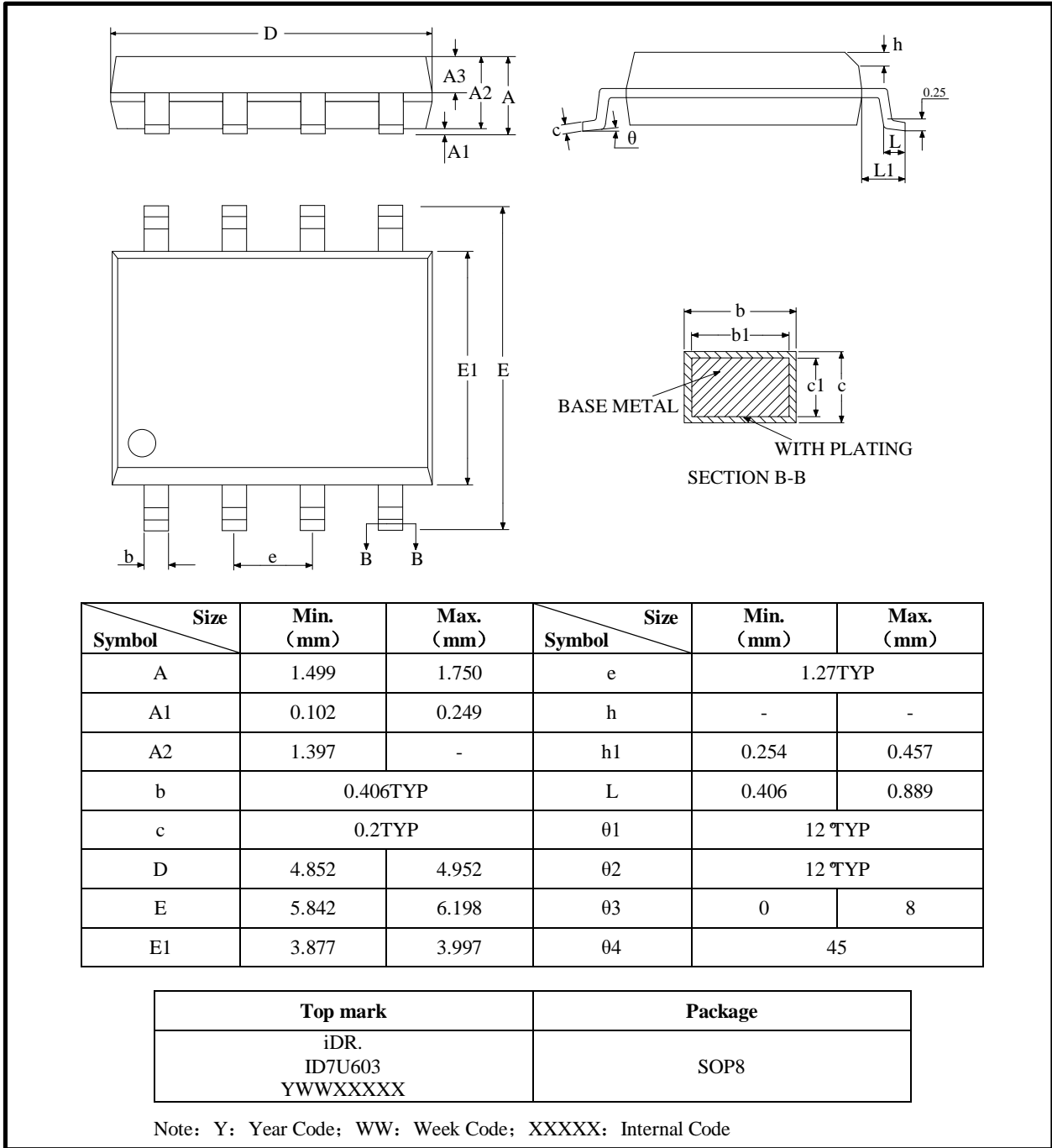


Fig.3 Dead-time waveform definitions

## Package Information

### Package Information SOP8



Notes:

1. This drawing is subjected to change without notice.
2. Body dimensions do not include mold flash or protrusion.

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